## 8550M

Rev.F Apr.-2017



### 描述 / Descriptions

SOT-23 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a SOT-23 Plastic Package.

### 特征 / Features

与8050M 互补。

Complementary pair with 8050M.

## 用途 / Applications

用于功率放大电路。

Power amplifier applications.

## 内部等效电路 / Equivalent Circuit



### 引脚排列 / Pinning



PIN1: Base PIN 2: Emitter PIN 3: Collector

## 放大及印章代码 / h<sub>FE</sub> Classifications & Marking

h <sub>FE</sub> Classifications Symbol	В	С	D		
h <sub>FE</sub> Range	85~160	120~200	160~300		
Marking	HY2B	HY2C	HY2D		



# 极限参数 / Absolute Maximum Ratings(Ta=25°C)

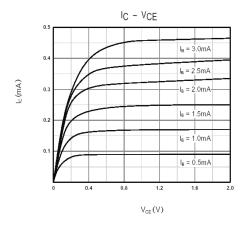
参数	符号	数值	单位
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	-40	V
Collector to Emitter Voltage	V <sub>CEO</sub>	-25	V
Emitter to Base Voltage	V <sub>EBO</sub>	-6.0	V
Collector Current	I <sub>C</sub>	-1.5	Α
Base Current	I <sub>B</sub>	-0.5	Α
Collector Power Dissipation	P <sub>C</sub>	625	mW
Junction Temperature	Tj	150	$^{\circ}$ C
Storage Temperature Range	T <sub>stg</sub>	<i>-</i> 55∼150	$^{\circ}$ C

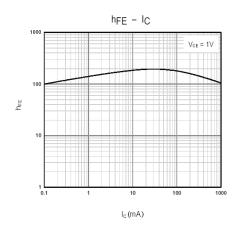
# 电性能参数 / Electrical Characteristics(Ta=25°C)

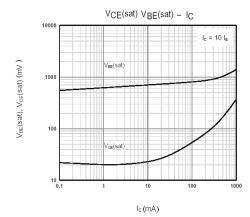
参数	符号	符号    测试条件		最小值	典型值	最大值	单位
Parameter	Symbol	Test Conditions		Min	Тур	Max	Unit
Collector to Base Breakdown Voltage	V <sub>CBO</sub>	I <sub>C</sub> =-0.1mA I <sub>E</sub> =0		-40			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	I <sub>C</sub> =-2.0mA	2.0mA I <sub>B</sub> =0				٧
Emitter to Base Breakdown Voltage	$V_{EBO}$	I <sub>E</sub> =-0.1mA	I <sub>C</sub> =0	-6.0			V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =-35V	I <sub>E</sub> =0			-0.1	μΑ
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =-6.0V	I <sub>C</sub> =0			-0.1	μΑ
OC Current Gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-1.0V	I <sub>C</sub> =-100mA	85		300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =-1.0V	I <sub>C</sub> =-800mA	40			
	h <sub>FE(3)</sub>	V <sub>CE</sub> =-1.0V	I <sub>C</sub> =-5.0mA	45			
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-800mA	I <sub>B</sub> =-80mA		-0.28	-0.5	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-800mA	$I_B$ =-80mA		-0.98	-1.2	V
Base-Emitter Voltage	$V_{BE}$	V <sub>CE</sub> =-1.0V	I <sub>C</sub> =-10mA		-0.66	-1.0	٧
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V	I <sub>C</sub> =-50mA	100	200		MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V f=1.0MHz	I <sub>E</sub> =0		15		pF

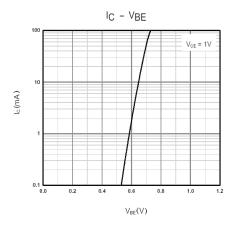


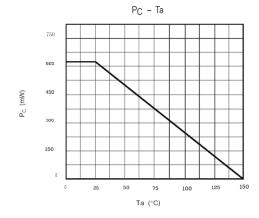
## 电参数曲线图 / Electrical Characteristic Curve

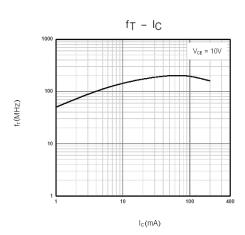










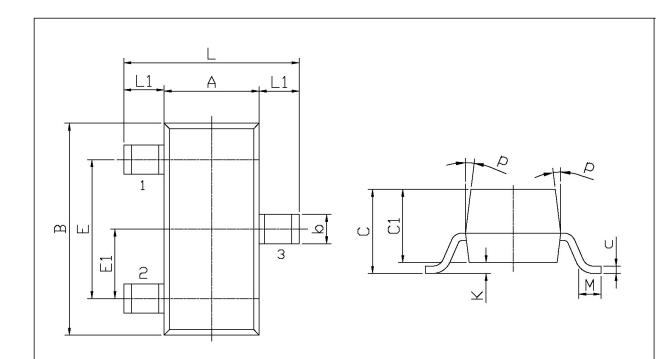




# 外形尺寸图 / Package Dimensions

S0T-23

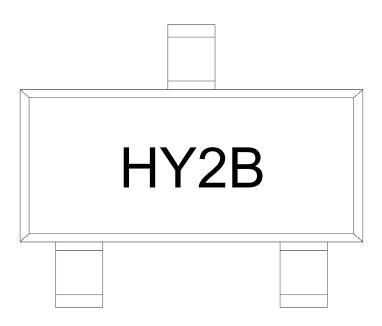
单位; mm



Symbol	Dimensions In Millmeters  Min Max		S	Dimensions In Millmeters		
Symbol			Symbol	Min	Max	
L	ณ	2.2 2.7		1.30Ma×		
L1	0.45 0.65		C1	0.90	1.20	
Α	1,15	1.50	_	0.05	0.20	
В	2,70	3.10	К	0	0.10	
E	1.70	2.10	М	0.20	OMIN	
E1	0.85	1.05	Р	7°		
b 0.35		0,55				



# 印章说明 / Marking Instructions



说明:

H: 为公司代码

Y2: 为型号代码

B: 为 h<sub>FE</sub> 档次代码

Note:

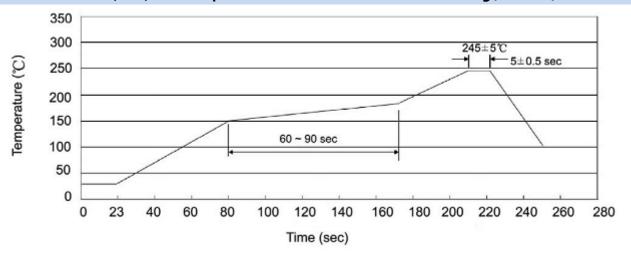
H: Company Code

Y2: Product Type Code

 $B: \qquad \quad h_{FE} \ Classifications \ Symbol \ Code$ 



## 回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



### 说明:

1、预热温度 25~150℃, 时间 60~90sec;

2、峰值温度 245±5℃, 时间持续为 5±0.5sec;

3、焊接制程冷却速度为 2~10℃/sec.

#### Note:

1.Preheating:25~150°C, Time:60~90sec.

2.Peak Temp.:245±5°C, Duration:5±0.5sec.

3. Cooling Speed: 2~10°C/sec.

### 耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度: 260±5℃ 时间: 10±1 sec. Temp.:260±5℃ Time:10±1 sec

### 包装规格 / Packaging SPEC.

### 卷盘包装 / REEL

	Package Type	units 包装数量				Dimension 包装尺寸 (unit: mm³)			
	封装形式	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
	SOT-23	3,000	10	30,000	6	180,000	7″ ×8	180×120×180	390×385×205

### 使用说明 / Notices